

Supplemental Information for
**Quantum oscillations in Noncentrosymmetric Weyl
semimetal SmAlSi**

Weizheng Cao(曹渭征)¹, Yunlong Su (苏云龙)¹, Qi Wang(王琦)^{1,2}, Cuiying Pei(裴翠颖)¹,
Lingling Gao (高玲玲)¹, Yi Zhao(赵毅)¹, Changhua Li (李昌华)¹, Na Yu(余娜)¹, Jinghui Wang(王
靖琿)^{1,2**}, Zhongkai Liu(柳仲楷)^{1,2}, Yulin Chen(陈宇林)^{1,2,3}, Gang Li(李刚)^{1,2**}, Jun Li (李军)^{1,2},
and Yanpeng Qi(齐彦鹏)^{1,2,4**}

¹School of Physical Science and Technology, ShanghaiTech University, Shanghai 201210, China

²ShanghaiTech Laboratory for Topological Physics, ShanghaiTech University, Shanghai 201210,
China

³Department of Physics, Clarendon Laboratory, University of Oxford, Parks Road, Oxford OX1
3PU, UK

⁴Shanghai Key Laboratory of High-resolution Electron Microscopy, ShanghaiTech University,
Shanghai 201210, China

** Corresponding authors. Y.Q. (qiyp@shanghaitech.edu.cn); J.W. (wangjh2@shanghaitech.edu.cn) or G. L. (ligang@shanghaitech.edu.cn)

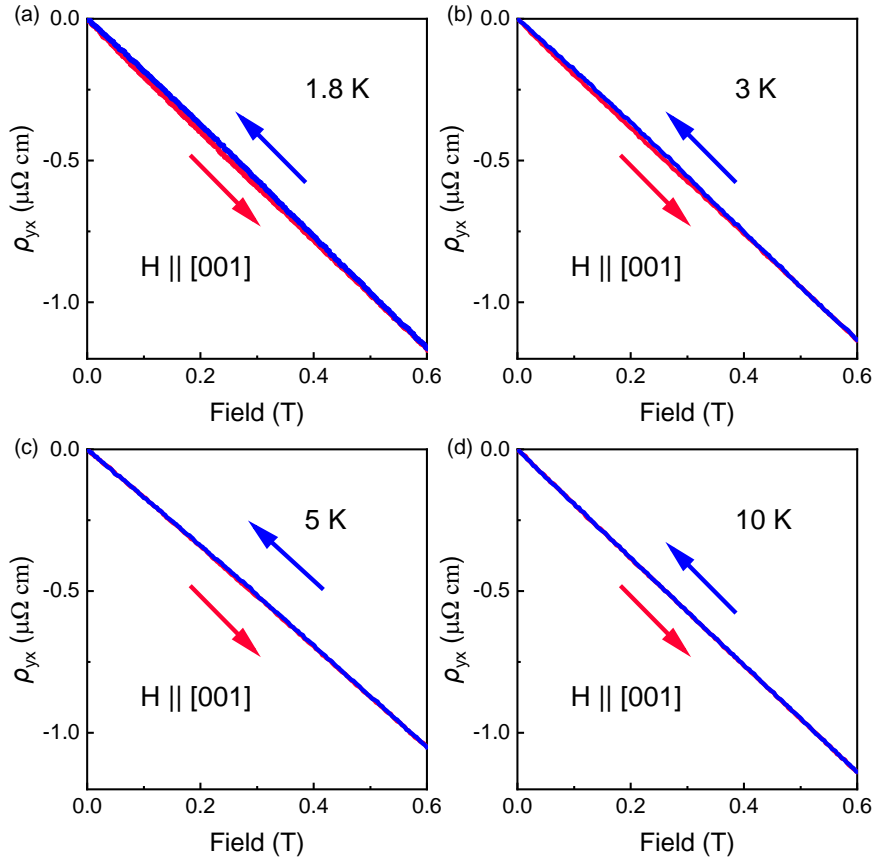


FIG. S1. (a - d) The Hall resistivity measured with magnetic along the [001] direction at 1.8K, 3K, 5K and 10K, respectively. The unusual Loop Hall Effect (LHE) is observed, and the LHE is suppressed with the temperature increasing. The Loop Hall effect is related to the relative positions of the Weyl point and the Fermi levels for CeAlSi.